

2SK2993

Chopper Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance : $R_{DS(ON)} = 82 \text{ m}\Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 20 \text{ S}$ (typ.)
- Low leakage current : $I_{DSS} = 100 \text{ }\mu\text{A}$ (max) ($V_{DS} = 250 \text{ V}$)
- Enhancement-mode : $V_{th} = 1.5 \sim 3.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics S	ymbol	Rating	Unit
Drain-source voltage	V_{DSS}	250	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	250	V
Gate-source voltage	$V_{GSS} \pm$	20	V
Drain current	DC (Not e 1)	I_D	20
	Pulse (Note 1)	I_{DP}	60
Drain power dissipation ($T_c = 25^\circ\text{C}$)	P_D	100	W
Single pulse avalanche energy (Not e 2)	E_{AS}	423	mJ
Avalanche current	I_{AR}	20	A
Repetitive avalanche energy (Note 3)	E_{AR}	10	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

Thermal Characteristics

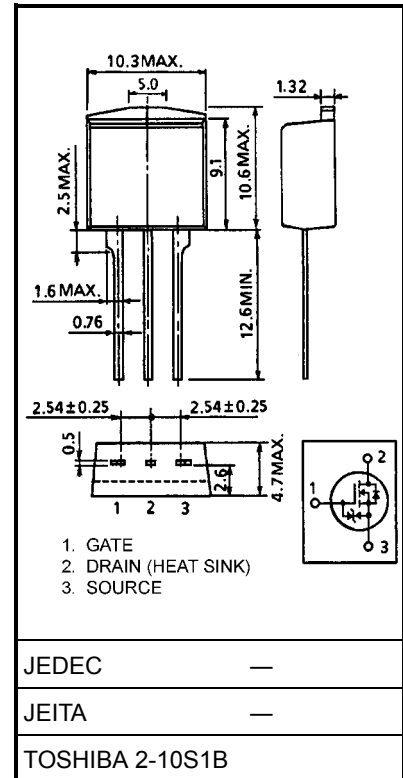
Characteristics S	ymbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	83.	$^\circ\text{C} / \text{W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

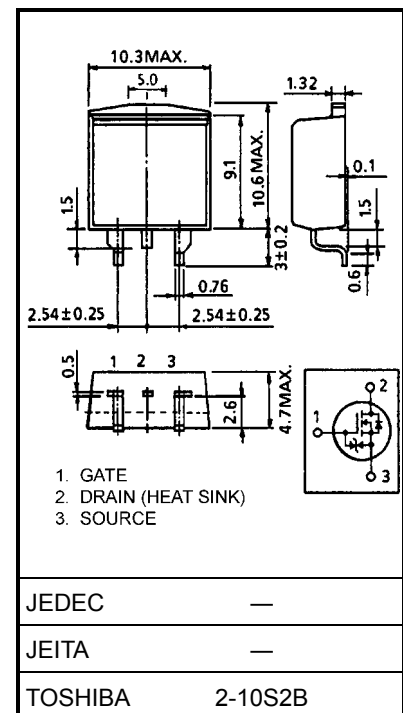
Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.79 \text{ mH}$, $I_{AR} = 20 \text{ A}$, $R_G = 25 \text{ }\Omega$

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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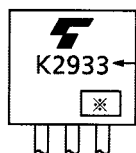
Electrical Characteristics (Ta = 25°C)

Characteristics S	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA	
Drain cut-off current	I_{DSS}	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	250	—	—	V	
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V	
Drain-source ON resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	—	82	105	m Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$	10	20	—	S	
Input capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	4000	—	pF	
Reverse transfer capacitance	C_{rss}		—	300	—		
Output capacitance	C_{oss}		—	1000	—		
Switching time	Rise time	t_r		15	—	ns	
	Turn-on time	t_{on}		—	35		—
	Fall time	t_f		—	30		—
	Turn-off time	t_{off}		—	180		—
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 200\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	—	100	—	nC	
Gate-source charge	Q_{gs}		—	70	—		
Gate-drain ("miller") Charge	Q_{gd}		—	30	—		

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics S	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Not e 1)	I_{DR}		—	—	20	A
Pulse drain reverse current (Not e 1)	I_{DRP}		—	—	60	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 20\text{ A}, V_{GS} = 0\text{ V}$	—	—	-2.0	V
Reverse recovery time	t_{rr}	$I_{DR} = 20\text{ A}, V_{GS} = 0\text{ V}$	—	300	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	3	—	μC

Marking

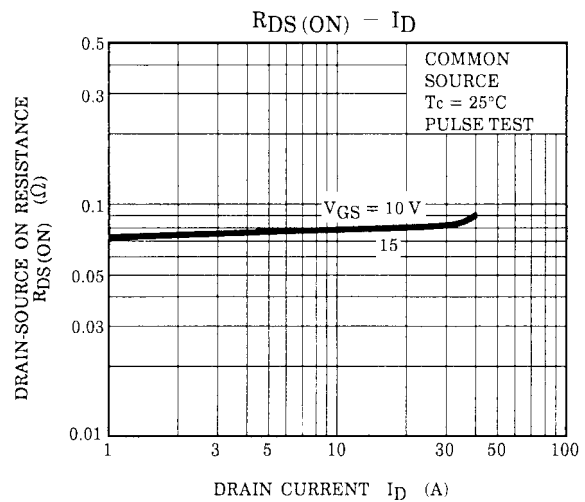
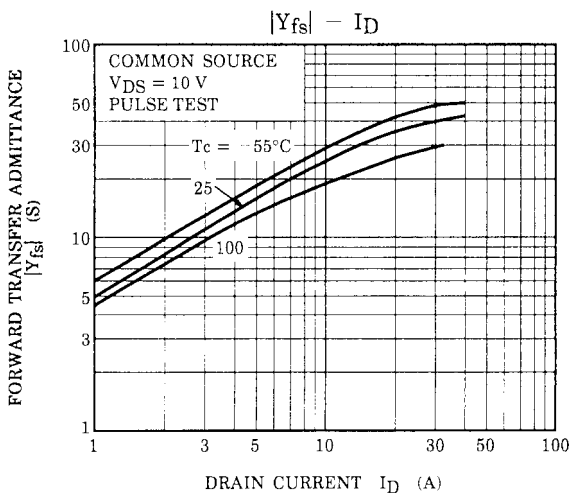
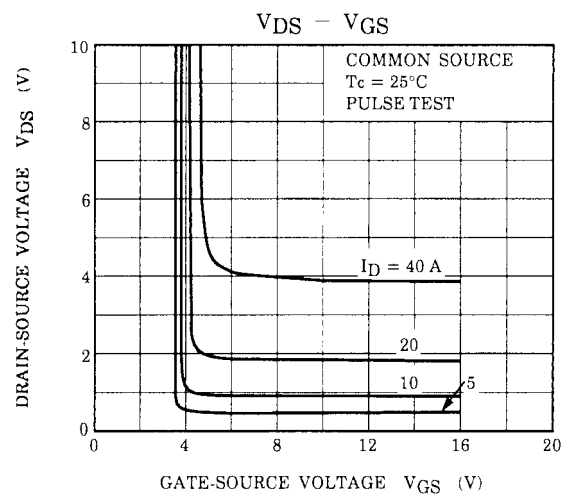
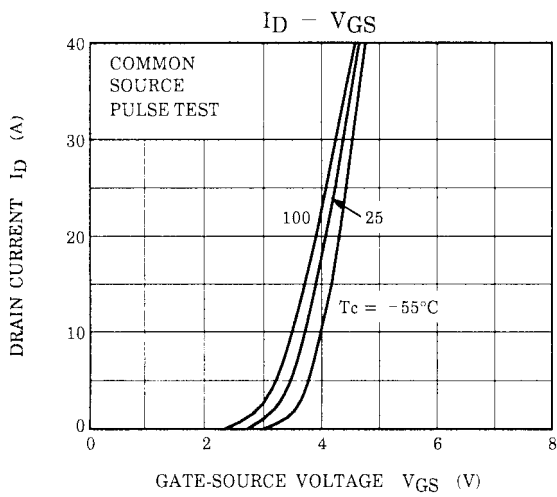
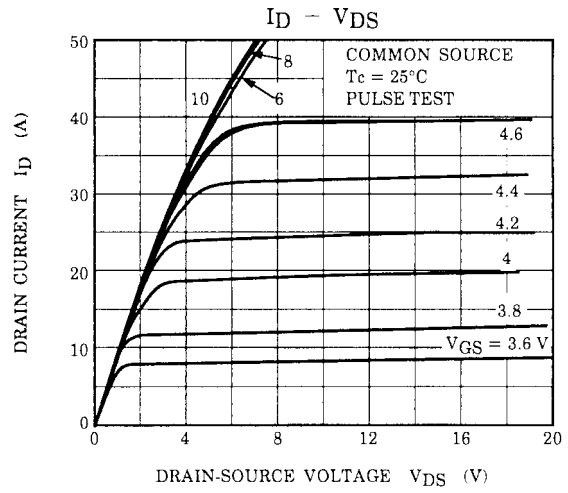
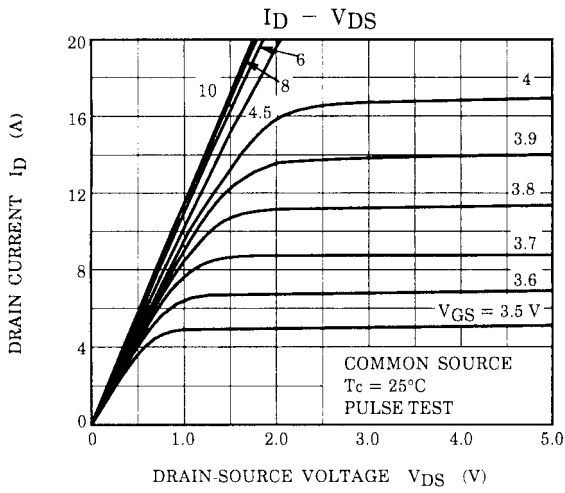


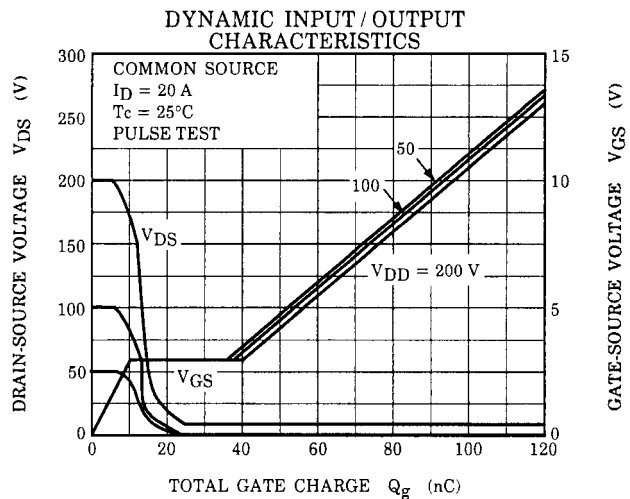
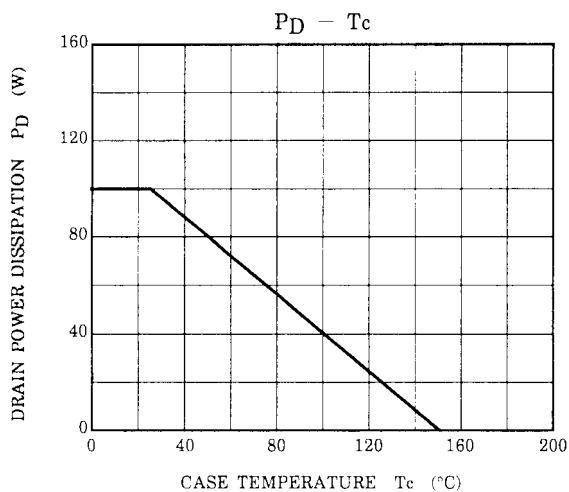
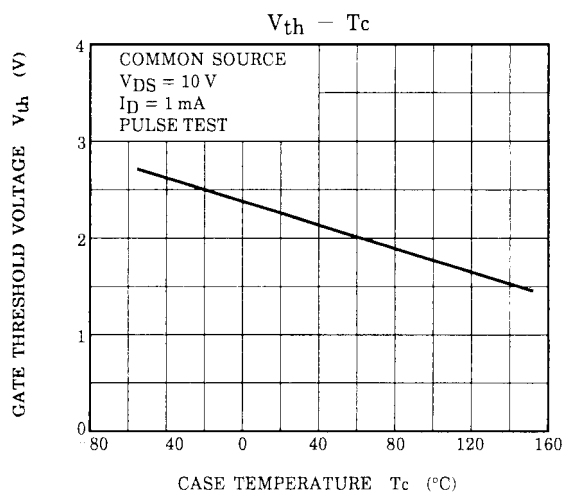
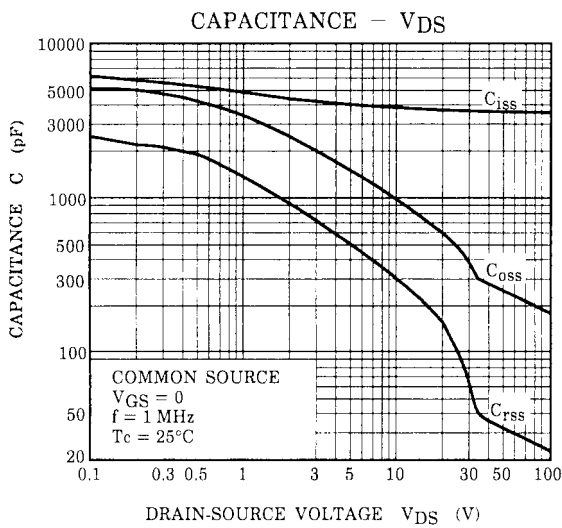
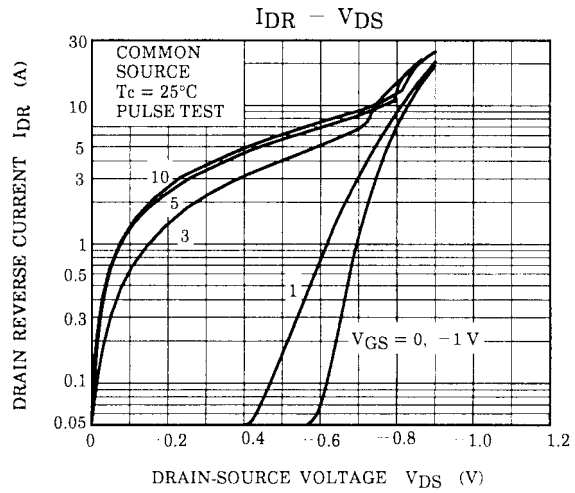
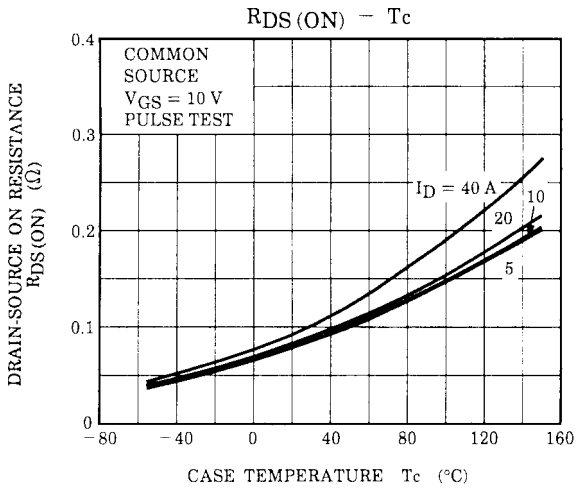
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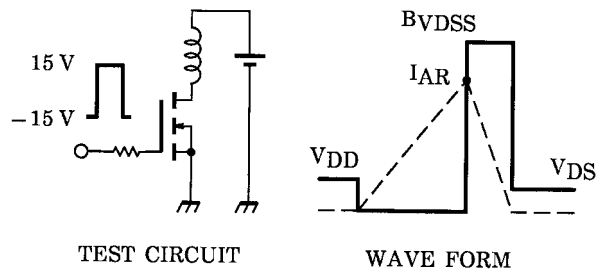
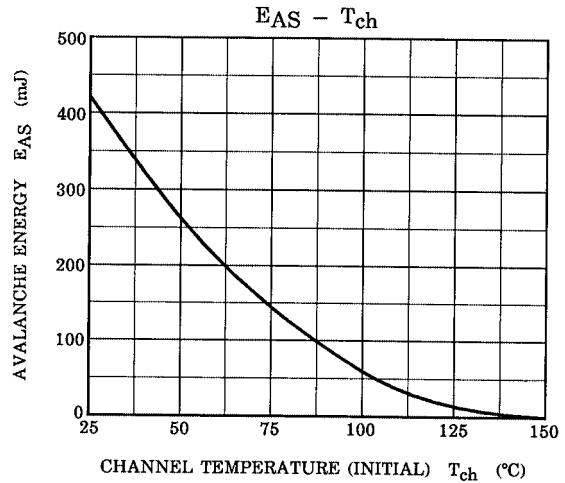
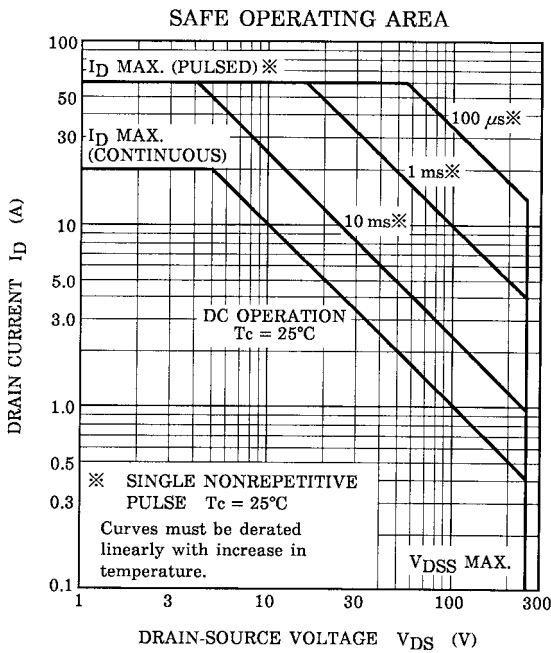
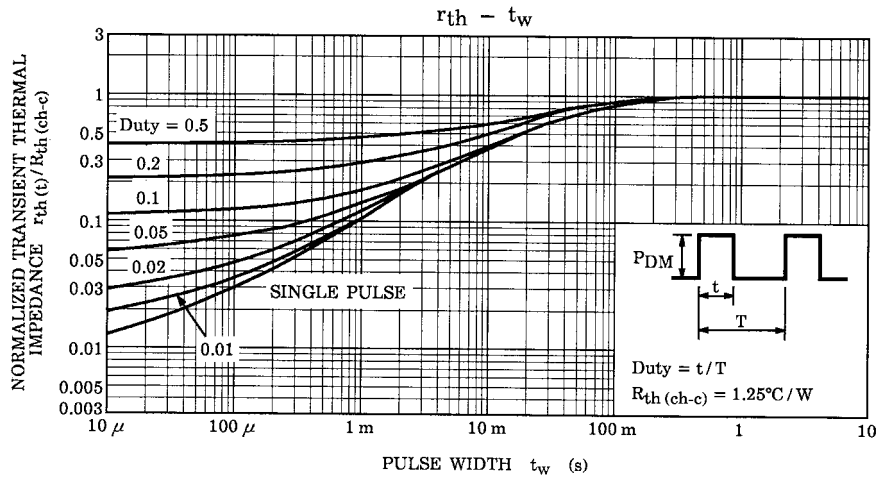
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







$R_G = 25 \Omega$
 $V_{DD} = 90 V, L = 1.79 mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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